

ABSTRACT

A semiconductor device has
a circuit board,
a ferroelectric capacitor arranged on said circuit
board, having a ferroelectric thin film and top and bottom
electrodes which are formed so as to hold said ferroelectric
thin film,

an insulating film formed on said circuit board so as
to cover said ferroelectric capacitor,

a metallic wiring film formed on said insulating film
so as to connect with either of said top and bottom
electrodes, and

a surface protective film formed so as to cover said
insulating film and said metallic wiring film, wherein

a synthetic stress working in a surface direction of
the ferroelectric thin film of said ferroelectric capacitor
is an extensional stress.